ABSTRACT OF THE DISCLOSURE

Method for Manufacturing Group III-V Compound Semiconductor

A method for manufacturing a group III-V compound semiconductor represented by the general formula $In_xGa_yAl_zN$ (where $x+y+z = 1$, $0 \leqq x \leqq 1$, $0 \leqq y \leqq 1$, and $0 \leqq z \leqq 1$) by metalorganic vapor phase epitaxy method is provided. The group III-V compound semiconductor has a semiconductor layer consisting of a p-type dopant-nondoped layer, and a semiconductor layer including a p-type dopant-doped layer. In the method, a reactor for growing the semiconductor layer consisting of a p-type dopant-nondoped layer and a reactor for doping a p-type dopant are mutually different.

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